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Photocatalytic splitting of water under visible-light irradiation over the NiOx-loaded Sm₂InTaO₇ with $4f-d^{10}-d^0$ configuration

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ABSTRACT

A new visible-light-response photocatalyst $\text{Sm}_2\text{InTaO}_7$ with $4f - d^{10} - d^0$ configuration crystallized in a cubic system with the space group Fd3m was synthesized by a solid-state reaction method. NiOx-loaded $\text{Sm}_2\text{InTaO}_7$ showed high photocatalytic activities for H₂ evolution from pure water under visible light irradiation ($\lambda > 400 \text{ nm}$). Changes in the photocatalytic activity with the calcination temperature of $\text{Sm}_2\text{InTaO}_7$ and the amount of NiOx loaded indicated that the combination of highly crystallized $\text{Sm}_2\text{InTaO}_7$ and a high dispersion of NiOx particles led to high photocatalytic activity. The high photocatalytic activity correlated with the lattice distortion. Density functional theory calculation indicated that strong dispersion from the hybridized In 5s 5p orbitals at the bottom of the conduction band was responsible for the high activity of photocatalyst Sm₂InTaO₇.

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1. Introduction

Since the discovery of photocatalytic splitting of water on TiO_2 electrodes by Fujishima and Honda in 1972 [1], the photocatalytic water splitting using solar energy and semiconductors to generate clean energy hydrogen has attracted increasing attention [2–5]. It is well known that the UV light occupies only about 4% of the whole solar energy while the visible light accounts for 43%. From the viewpoint of a potentially efficient utilization of solar energy, the development of photocatalysts with visible-light response will therefore be valuable for application to H₂ production using solar energy. Oxide materials are plausible candidates of the new photocatalytic material in relation to their higher chemical stability and easier preparation compared with non-oxide materials.

Some tantalates with octahedrally coordinated d^0 configuration, such as $ATaO_3$ (A=Li, Na, K) [6,7], $Sr_2Ta_2O_7$ [8], RbNdTa₂O₇ [9], have been well known as promising semiconductor photocatalysts in the last decades. Various indates with octahedrally coordinated d^{10} configuration, such as MIn_2O_4 (M=Ca, Sr, Ba) [10–12] and $Sr_{1-x}M_xIn_2O_4$ (M=Ca, Ba) [13], have also been reported as photocatalysts for water splitting. However, these Ta⁵⁺- or In³⁺-containing compounds are not active under visible light. On the other hand,

the partly filled 4*f* shell plays a key role in photocatalytic reactions and the 4f orbital electrons of lanthanides have the effect on reducing the band gap energy of lanthanide complex oxides [9, 14–16]. Especially, some pyrochlore-type $A_2B_2O_7$ (A and B are metal ions) compounds, such as Ln₂Zr₂O₇ (Ln=Sm, Nd) [16] and In₂BiTaO₇ [17], have recently been reported as photocatalysts for water splitting under visible light irradiation. Based on above consideration, if appropriate lanthanides ions, Ta⁵⁺ and In³⁺ are incorporated with an pyrochlore-type crystal structure of semiconductor, a new visible-light-driven photocatalyst with suitable band edges for water splitting might be obtained. It will be interesting to use composite metal oxides involving lanthanide, the *p*- and *d*-block metal ions, i.e., metal oxides with $4f - d^{10} - d^0$ configuration, for the development of photocatalysts for water splitting under visible light irradiation since it is thought that hybridization of the sp orbitals of *p*-block metal ions and the partly filled 4f orbital electrons of lanthanides may have a significant effect on the density of states and energy dispersion in the conduction bands and the band gap energy, respectively.

In this paper, we report a new pyrochlore-type $(A_2B_2O_7)$ photocatalyst Sm₂InTaO₇ with $4f-d^{10}-d^0$ configuration, in which the *B* site as core element site is occupied by In³⁺ and Ta⁵⁺ ions randomly in the charge-balanced manner. Its photocatalytic activity for water splitting was assessed after NiOx-loading under visible light irradiation ($\lambda > 400$ nm). The optimal conditions for high photocatalytic activity was compared with that of a pyrochlore-type metal oxide, Sm₂Zr₂O₇ [16], with the $4f-d^0$ configuration, and the advantages of the $4f-d^{10}-d^0$ configuration were

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discussed on the basis of the crystal structure and band structures calculated by the DFT method.

2. Experimental

The polycrystalline samples of the Sm₂InTaO₇ photocatalysts were synthesized by a solid-state reaction method. In₂O₃, Sm₂O₃ and Ta₂O₅ with purity of 99.99% were used as starting materials. Sm₂O₃ was dried before use. The fully mixed chemical powder in a stoichiometric ratio were sintered in air for 52 h in the temperature range 1373–1673 K with intermediate regrinding to complete reaction. The polycrystalline samples of the Sm₂Zr₂O₇ photocatalysts were prepared by the reported procedure [16]. To introduce active sites on the surface of the photocatalyst particles, partially oxidized nickel was loaded on the surface of the photocatalyst particles from aqueous Ni(NO₃)₂ solution by an impregnation method. The Ni-loaded photocatalyst was first calcined at 350 °C for 1 h in air and reduced in a H₂ atmosphere at 500 °C for 2 h and then treated in an O₂ atmosphere at 200 °C for 1 h. The double-layered structure of metallic Ni and NiO (denoted NiOx) was formed on the surface of photocatalyst by a reduction-oxidation procedure [2,18].

The crystal structure of Sm₂InTaO₇ was analyzed by the powder X-ray diffraction (D/Max 2500 VB+, Japan) with CuKa radiation (λ =0.154056 nm). The data were collected at 295 K with a step scan procedure in the range of 2θ =5–100°. The step interval was 0.02° and the scan speed was 1° min⁻¹. The chemical composition of the compound was determined by field emission scanning electron microscope-X-ray energy dispersion spectrum (SEM-EDS) (Sirion 200, Philips, Netherlands) and inductively coupled plasma atomic emission spectrometers (ICP-AES) (Leeman Prodigy, USA). Surface area and pore volume of the powder sample were measured on a surface area analyzer (Autosorbi/monosorb, Ouantachrme, America) by nitrogen absorption at 77K using the Brunauer-Emmett-Teller (BET) method. Saturated adsorbed amount of O₂ of the powder sample was measured in O₂ ambience by Perkin-Elmer thermogravimetric analysis system. The diffuse reflectance spectra (DRS) of the photocatalyst samples were obtained using a UV-vis scanning spectrophotometer (TU-1901, Beijing-Purkinje, China) at room temperature, and were converted from reflectance to absorbance by the Kubelka-Munk method. The surface chemical states of the photocatalyst samples were measured by X-ray photoelectron spectroscopy (XPS) (ESCALAB MK, England). The microstructures of NiOx on the surface of the photocatalyst samples were measured by transmission electron microscopy (TEM) (TecnaiG20ST, PHILIPS, Netherlands).

The photocatalytic reaction was examined using a closed gas circulation system. The NiOx-loaded photocatalyst (1g) was suspended in distilled water (570 mL) in a quartz inner-irradiation reaction vessel. The reactant solution was evacuated several times to remove air completely prior to irradiation using a 250W high-pressure Xe arc lamp. For visible irradiation ($\lambda > 400$ nm) [5], a circulating sodium nitrite (NaNO₂) aqueous solution (2 M) cooled by a flow of cooling water was inserted in the light path used to block ultraviolet (UV) light and remove heat produced by xenon lamp. Moreover, the whole reaction vessel was fooled by a flow of cooling water to make the reactant solution maintained at room temperature during the reaction. The gases evolved in the reaction were analyzed by gas chromatography (Shimadsu GC-8A, Tokyo, Japan; Ar carrier).

The theoretical calculation of the electronic structure of the Sm₂InTaO₇ was carried out based on density function theory with plane-wave pseudopotential method and generalized gradient approximation [19]. The core electrons were replaced by the norm-conserving pseudopotential O $2s^22p^4$, In $4d^{10}5s^25p^1$, Ta $4f^{14}5d^36s^3$, and Sm $4f^65s^25p^66s^2$ electrons were treated explicitly.

The kinetic energy cutoff was set to 300 eV, and the unit cell includes ($\text{Sm}_2\text{InTaO}_7$)₂ structure. The lattice constant and the atomic positions were optimized with finite basis set correction.

3. Results and discussion

Fig. 1 shows the X-ray diffraction patterns of Sm₂InTaO₇ calcined at different temperatures. The power X-ray diffraction analysis showed that Sm₂InTaO₇ calcined at 1573 K and 1673 K was a single phase. In the case of the samples calcined at 1373 K, most of the peaks in X-ray diffraction patterns were attributed to Sm₂InTaO₇, but relatively weak peaks due to In₂O₃ were also observed. With increasing temperature from 1373 to 1673 K, the major peaks became narrower and their intensity increased. The chemical composition of the Sm₂InTaO₇ compound calcined at 1573 K was determined using characteristic X-rays of InL_{α} , SmL_{α} , and TaL_{α} . The composition content was decided using the ZAF (element number, absorption and fluorescence corrections) quantification method. The SEM-EDS analysis showed that the compound had a homogenous atomic distribution with no other additional elements. An average atomic rate of Sm:In:Ta=2.00:0.97(2):1.03(3) was obtained from measurements made at several different points. The exact composition of Sm₂InTaO₇ prepared at 1573 K was also measured by ICP. The ICP-AES chemical composition analysis showed that the chemical formula was determined to be Sm1.99In0.98Ta1.02O7 (normalized to seven oxygens), which was basically in agreement to the nominal starting stoichiometric ratio.

Full-profile structure refinement of the collected powder diffraction data for Sm_2InTaO_7 calcined at 1573 K was performed using the Rietveld program FULLPROF [20]. Positional parameters and isotropic thermal parameters of all atoms of the Sm_2InTaO_7 compound were refined (Table 1). The outcomes of the final refinement indicated that Sm_2InTaO_7 was crystallized in a cubic system with space group *Fd3m*, and the lattice parameter was a=10.5448(2)Å. All of the reflection peaks could be successfully indexed based on the lattice parameter and the space group (see



Fig. 1. X-ray diffraction patterns and indexed result of Sm_2InTaO_7 calcined at 1373 K (a), 1573 K (b), and 1673 K (c).

Table 1

Structural parameters of Sm_2InTaO_7 obtained by the Rietveld structure refinement. Sm_2InTaO_7 was prepared by calcination at 1573 K.

Atom	Site	x	у	Z	$U_{\rm iso}({\rm \AA})$	Occupancy
Sm	16(<i>d</i>)	0.5000	0.5000	0.5000	0.0123 (5)	1.0
In/Ta	16(<i>c</i>)	0.0000	0.0000	0.0000	0.0028 (8)	0.5
O1	48(<i>f</i>)	0.3302 (3)	0.1250	0.1250	0.010 (4)	1.0
O2	8(<i>b</i>)	0.3750	0.3750	0.3750	0.007 (6)	1.0



Fig. 2. UV-vis diffuse reflectance spectrum (DRS) of Sm_2InTaO_7 calculated at 1373 K (a), 1573 K (b), and 1673 K (c).

Fig. 1). The result of refinements yielded *R* factors, R_p =7.46%, R_{WP} =10.1% in space group *Fd*3*m* when the O atoms are included in the model.

Fig. 2 shows the UV-vis diffuse reflectance spectrum (DRS) of Sm₂InTaO₇ calcined at different temperatures. Sm₂InTaO₇ photocatalyst showed obvious absorption in visible light region $(\lambda > 400 \text{ nm})$ irrespective of the calcination temperature, which indicated that the prepared Sm₂InTaO₇ had the ability to respond to visible light. An average absorption of < 20% was obtained from 500 to 700 nm and the absorption in wavelength < 420 nm attenuated with increasing calcination temperature and was dramatically reduced upon calcination at 1573 K. This was mainly because it eliminated impurities In₂O₃ and the crystallite size increased with increasing calcination temperature, which resulted in decreasing of light absorption. It should be noted that the onset of the absorption edges of Sm₂InTaO₇ became unclear because several absorptions overlap in visible light range ($\lambda > 400$ nm). This could be attributed to internal transitions in a partly filled Sm 4f shell. Actually, the spectra in this region were in accord with those observed in Sm₂O₃ [21]. Two similar results for the overlap with another absorption band had also been reported for the RbLnTa₂O₇ (Ln=Pr and Nd) [9] and Bi₂RNbO₇ (R=Y, rare earth) system [22]. The band gaps of the materials were calculated from the absorption spectra by using the equation: $\alpha(hv) = A(hv - Eg)^{n/2}$, where α , v, Eg and A are absorption coefficient, light frequency, band gap, and a constant, respectively. The value of *n* was determined to be 1 from the absorption spectra, indicating that the optical transitions were all directly allowed for Sm₂InTaO₇. The band gap of Sm₂InTaO₇ prepared at 1573 K was determined to be about 2.81 eV.

Fig. 3 shows photocatalytic H₂ evolution from pure water (570 ml) over 1 wt% NiOx-loaded Sm₂InTaO₇ (1.0 g) under visible light irradiation ($\lambda > 400$ nm). The reaction was repeated three times. Clearly, the amount of evolved H₂ gas increased linearly with an increase of irradiation time in three run. The photocatalytic activity slightly decreased in the second run, but no further attenuation occurred in the third run, indicating that NiOx-loaded Sm₂InTaO₇ were stable. The XRD patterns of Sm₂InTaO₇ showed no difference before and after the photocatalytic H₂ evolution, also indicating the photocatalyst was stable under the present working condition. The average rate of H₂ evolution in the third run (after about 16 h of reaction time) was about 4.6 µ mol/h for 1 wt% NiOxloaded Sm₂InTaO₇. The turnover number of reacted electrons to the amount of Ni loaded on the surface of Sm₂InTaO₇ reached about 1.5 at 24 h of the reaction time. No H₂ evolution was detected when the light was turned off ('dark test') and the reaction cell was reevacuated. This result excluded the possibility of H₂ generation from the 'mechano-catalytic mechanism' [23]. All the aforementioned results implied that the H₂ evolution was inherently the result of photocatalytic reaction over the Sm₂InTaO₇ oxide semiconductor.



Fig. 3. Photocatalytic H_2 evolution over 1.0 wt% NiOx-loaded Sm_2InTaO_7 under visible-light irradiation. Sm_2InTaO_7 was prepared by calcinations at 1573 K.



Fig. 4. Photocatalytic activity of 1.0 wt% NiOx-loaded Sm_2InTaO_7 for H_2 evolution as a function of the calcinations temperature of Sm_2InTaO_7 .

Fig. 4 shows the photocatalytic activity of 1 wt% NiOx-loaded Sm₂InTaO₇ for H₂ evolution as a function of the calcination temperature used during Sm₂InTaO₇ preparation. The activity increased with increasing temperature from 1373 K and reached a maximum at 1573 K, beyond which it rapidly decreased. The surface area was 0.67-0.78 m²/g for calcination below 1573 K and decreased to 0.47 m²/g for calcination at 1673 K. The reason for the dependence of the photocatalytic activity on the calcination temperature of Sm₂InTaO₇ could be explained as follows: when the calcination temperature was below 1573 K where the activity increased with increasing temperature from 1373 to 1573 K, the XRD images (Fig. 1) showed a considerable increase in the crystallite size of Sm₂InTaO₇ according to a narrowing of the X-ray diffraction peaks. These results demonstrated that the crystallization of Sm₂InTaO₇ was responsible for activity enhancement, since it eliminated impurities and structural imperfections that frequently acted as traps for charge recombination. When the calcination temperature was above 1573 K, 1 wt% NiOx on the Sm₂InTaO₇ surface was excess due to the reduction of the surface area of Sm2InTaO7 and the relationship between the amount of NiOx loaded and photocatalytic activity (see Fig. 5) indicated that the excess NiOx on the Sm₂InTaO₇ surface lowered the activity. The agglomeration of NiOx particles readily occurred (see Fig. 6) when large amounts of NiOx were loaded for a small surface area of Sm₂InTaO₇, producing large NiOx particles, which resulted in decrease of the density of photocatalytic active sites. Fig. 7 shows a TEM image of the 1 wt% NiOx/Sm₂InTaO₇ photocatalyst prepared by calcination at 1573 K. Nearly spherical NiOx particles were distributed on the surface of Sm₂InTaO₇ and the



Fig. 5. Photocatalytic activity of NiOx-loaded Sm_2InTaO_7 for H_2 evolution as a function of the amount of NiOx loading. Sm_2InTaO_7 was prepared by calcinations at 1573 K.



Fig. 6. TEM micrograph of $1.0\,wt\%$ $NiOx/Sm_2InTaO_7$ photocatalyst prepared by calcinations at 1673 K.

sizes of NiOx particles were about 16 nm. These results indicated that a high dispersion of small NiOx particles was essential for high photocatalytic performance of NiOx-loaded Sm₂InTaO₇.

The XPS spectra of 1 wt% NiOx/Sm₂InTaO₇ before and after photocatalytic water splitting shown in Fig. 8 reveal the chemical status of nickel on the surface of Sm₂InTaO₇. It is known that the binding energies of the Ni $2P_{3/2}$ level for metallic nickel and NiO were 852.9 and 855.8 eV, respectively [24]. The binding energy peaks of the Ni $2P_{3/2}$ level for NiOx/Sm₂InTaO₇ before photocatalytic water splitting was 854.6 eV (shown in Fig. 8 (a)). The binding energy value was attributed to a combination of NiO and Ni, indicating that the formation of partially oxidized nickel as an enhancer of catalytic activity. The Ni $2P_{3/2}$ level for NiOx/ Sm₂InTaO₇ after photocatalytic water splitting exhibits a slight positive shift to 856.1 eV (shown in Fig. 8(b)), indicating that Ni(OH)₂ was formed after photocatalysis in aqueous solution [25].

However, no sign of O_2 evolution was observed in these experiments with NiOx-loaded Sm₂InTaO₇ photocatalysts. The same phenomenon has arisen over TiO₂ [26], Bi₂InNbO₇ [27], *M*Co_{1/3} Nb_{2/3}O₃ (*M*=Ca, Sr, and Ba) [28], and so on. On the one hand, it was proposed that there were both physisorbed and chemisorbed O₂ molecules on the surface of TiO₂ through low-energy photon irradiation, where the physisorbed O₂ was produced through the neutralization of chemisorbed O₂⁻ species by photogenerated holes



Fig. 7. TEM image of the $1 \text{ wt\% NiO}x/\text{Sm}_2\text{InTaO}_7$ photocatalyst prepared by calcinations at 1573 K.



Fig. 8. Ni 2p XPS spectra of 1 wt% NiOx/Sm₂InTaO₇: (a) before photocatalytic water splitting, and (b) after photocatalytic water splitting. Asterisks denote positions of the satellite peaks.

[26]. On the other hand, saturated adsorbed amount of O_2 had been measured by an indirect method (thermogravimetric analysis). Saturated adsorbed amount of O_2 for 1 wt% NiOx-loaded Sm₂InTaO₇ at 305 K was about 100 μ mol/g. Oxygen evolution should be very small in this experiment. Therefore, it was completely possible to notice no oxygen evolution was observed from pure water in this experiment. In addition, a series of the diffusions of these physisorbed and chemisorbed oxygen molecules along or over the crystalline boundaries also may be responsible for the 'absent' oxygen [29]. Further study of the photoadsorption of oxygen on these samples under visible light irradiation is in progress, which is believed to supply more concrete information.

As a comparison, the reaction of H₂ evolution over NiOx-loaded $Sm_2Zr_2O_7$ photocatalyst was carried out under the same condition. As shown in Fig. 9, the activity of NiOx-loaded $Sm_2Zr_2O_7$ was low. The rates of H₂ evolution over NiOx-loaded $Sm_2Zr_2O_7$ was 0.33 μ mol/h. The surface area of $Sm_2Zr_2O_7$ prepared by a solution reaction method was $6.36 \, m^2/g$ while the surface area of Sm_2InTaO_7 prepared by the solid-state method was only 0.67 m^2/g , indicating that the surface area was not the most important factor in deciding the different activities of the both photocatalysts.

It is generally believed that the crystal structure of photocatalyst play a crucial role in the photocatalytic activities. The schematic structural diagram of Sm₂InTaO₇ with pyrochlore-type



Fig. 9. Photocatalytic H₂ evolution over 1.0 wt% NiOx-loaded $Sm_2Zr_2O_7$ under visible-light irradiation. $Sm_2Zr_2O_7$ was prepared by a solution reaction method.



Fig. 10. Schematic structural diagram of $\text{Sm}_2\text{InTaO}_7$. $\text{Sm}_2\text{InTaO}_7$ consist of a threedimensional network structure of corner-linked $MO1_6$ (M=In and Ta) octahedral, connecting each other into [$MO1_3$]_a chains along [001].

structure is depicted in Fig. 10. It shows that the whole structure, similar to that of the Bi₂InNbO₇ compound [30], consists of the three-dimensional network of corner-linked MO1₆ (M=In and Ta) octahedra. The $MO1_6$ octahedra connect each other into $[MO1_3]_a$ chains along [001] and the Sm ions are located in between MO1₆ octahedral. Both the InO₆ and TaO₆ octahedrons in Sm₂InTaO₇ are heavily distorted. The distortion of BO₆ polyhedra in $A_2B_2O_7$ -type pyrochlore structures results in their lattice distortion which is one of the important parameter for charge separation and contributes to enhance the photocatalytic activity [8,31]. A correlation between photocatalytic activity and lattice distortion has been demonstrated in a series of pyrochlore-type structure metal oxide photocatalysts [32]. Information on the lattice distortion can be obtained from the O (48f) parameter x in the pyrochlore-type $A_2B_2O_7$ structure. The lattice distortion is equal to 0.375—the O (48f) parameter x [32]. For Sm₂Zr₂O₇, x=0.3359 [16], the lattice distortion was evaluated to be 0.0391 while the lattice distortion was evaluated to be 0.0448 for the Sm₂InTaO₇ photocatalyst. Thus, the present results for the NiOx-loaded Sm₂InTaO₇ showing high photocatalytic performance were in line with the correlation between activity and lattice distortion. Due to the presence of two metal ions with different sizes in the same site in the unit cell, the ease of formation of distorted octahedral units was the advantage of $4f-d^{10}-d^0$ composite metal oxides over metal oxides with the $4f-d^0$ configuration.

It is also generally believed that the band structure of photocatalyst play a decisive role in the photocatalytic activities. Prokofiev et al. [33] had studied periodicity in the optical band gap variation of rare earth sesquioxides. According to their results, the occupied 4f band in rare earth sesquioxides lay above the O 2p level, and thus the 4f-d transition determined the band gaps. The same consideration may be made for the Sm₂InTaO₇ compound. In addition, 5s and 5*p* orbitals of In^{3+} with octahedrally coordinated d^{10} configuration also may contribute to the conduction band of Sm₂InTaO₇. To confirm above consideration, the theoretical calculation of the electronic structure of the Sm2InTaO7 was carried out based on density function theory with plane-wave pseudopotential method and generalized gradient approximation. Structural parameters of Sm₂InTaO₇ obtained by the Rietveld structure refinement were used in DFT calculation. As the Sm 4f orbitals had smaller overlap and lower ionization potential, the self-consistent field (SCF)



Fig. 11. Band description and DOS for Sm₂InTaO₇.



Fig. 12. Total and partial DOS of Sm₂InTaO₇ around the bottom of the conduction band.

convergence was not good. Therefore, a fractional occupation technique was employed, which allows for the withdrawal and accumulation of a small amount of electron density in the top of the valence band and bottom of the conduction band [34]. Fig. 11 shows the band structure and density of state (DOS) of Sm₂InTaO₇. The top of the valence band (the Fermi level) is set to be zero on the ordinate. Very strong and narrow double peaks in DOS represented the localized character of Sm 4f levels. The Sm 4f bands existed above the top of the O 2p band and the valence band edge of Sm₂InTaO₇ became higher to decrease Eg. The occupied bands were the Sm 5s, O 2s+Sm 5p, O 2p+In 5s+Ta 5d, and Sm 4f bands in increasing order of energy, where the last was the valence band. The bottom of the unoccupied level (conduction band) was composed of the In 5s+In 5*p*, and Ta 5*d* atomic orbitals in the order of increasing energy. Both the valence band maximum and the conduction band minimum were located at the Q point, indicating that Sm₂InTaO₇ was a direct band gap semiconductor. The valance band was rather flat, and its dispersion was small. By contrast, the conduction band had a strong dispersion. The DFT calculation indicated the band gap of Sm₂InTaO₇ was 2.0 eV. The value was smaller than that obtained experimentally, which should be pointed out as a common feature of DFT calculations. This underestimation was an artifact of the GGA method used for this calculation [35]. To obtain more clear and exact information on the conduction band of Sm₂InTaO₇, partial DOS of Sm₂InTaO₇ around the bottom of the conduction band was shown in Fig. 12. The bottom of the CB in Sm₂InTaO₇ were composed of the hybridized In 5s and 5p orbitals, which revealed that Sm₂InTaO₇ had partial characteristic electronic structure of a d^{10} semiconductor. This result was obviously different from the Zr 4d orbital contributing mainly at the bottom of the CB in $Sm_2Zr_2O_7$ [16]. The hybridized In 5s and 5p orbitals (see Fig. 11) led to a strong dispersion. In the electron transfer from the Sm 4f orbital to the hybridized In 5s5p orbitals upon illumination, the strong dispersion in the conduction bands generated photoexcited electrons with high mobility, which was evidently associated with the high photocatalytic performance of NiOx-loaded Sm₂InTaO₇. Thus, from a viewpoint of band structures, the contribution of In 5s5p to the conduction bands was responsible for the high photocatalytic activity of NiOx-loaded Sm₂InTaO₇. The contribution of the sp orbitals of *p*-block metal ions to the conduction bands was also the advantage of $4f-d^{10}-d^0$ composite metal oxides over metal oxides with the $4f-d^0$ configuration.

4. Conclusions

The pyrochlore-type compound Sm_2InTaO_7 with $4f-d^{10}-d^0$ configuration was synthesized by a solid-state reaction method. The Sm₂InTaO₇ was found to be a new stable visible-lightresponse photocatalyst for H₂ evolution from pure water after NiOx-loading and the combination of well-crystallized Sm₂InTaO₇ with highly dispersed NiOx particles resulted in high photocatalytic performance. The $4f - d^{10} - d^0$ configuration was useful for photocatalysis from the viewpoint of both crystal and electronic structures.

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Appendix A. Supplementary material

Supplementary data associated with this article can be found in the online version at doi:10.1016/j.jssc.2009.10.023.

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